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(21) International Application Number: PCT/US96/11184 (22) International Filing Date: 1 July 1996 (01.07.96) (30) Priority Data: 08/498,028 3 July 1995 (03.07.95) US (71) Applicant (for all designated States except US): INTEL CORPORATION [US/US]; 2200 Mission College Boulevard, Santa Clara, CA 95052 (US). (72) Inventors; and (75) Inventors/Applicants (for US only): THOMPSON, Scott [US/US]; 19635 N.W. Rock Creek Way, Portland, OR 97229 (US). BOHR, Mark, T. [US/US]; 19475 S.W. Suncrest, Aloha, OR 97007 (US). PACKAN, Paul, A. [US/US]; 15025 S.W. Gibraltar Court, Beaverton, OR 97007 (US). (74) Agents: TAYLOR, Edwin, H. et al.; Blakely, Sokoloff, Taylor & Zafman, 7th floor, 12400 Wilshire Boulevard, Los Angeles, CA 90025-1026 (US).	(81) Designated States: AL, AM, AT, AT (Utility model), AU, AZ, BB, BG, BR, BY, CA, CH, CN, CZ, CZ (Utility model), DE, DE (Utility model), DK, DK (Utility model), EE, EE (Utility model), ES, FI, FI (Utility model), GB, GE, HU, IL, IS, JP, KE, KG, KP, KR, KZ, LK, LR, LS, LT, LU, LV, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SK (Utility model), TJ, TM, TR, TT, UA, UG, US, UZ, VN, ARIPO patent (KE, LS, MW, SD, SZ, UG), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, ML, MR, NE, SN, TD, TG). Published <i>With international search report.</i> This Sheet Has Been Replaced	
(54) Title: LOW DAMAGE SOURCE AND DRAIN DOPING TECHNIQUE		
(57) Abstract A process for fabricating a source and drain region which includes a more lightly doped source and drain tip region (40) immediately adjacent to the gate (11) and a more heavily doped main portion (41) of the source and drain region spaced apart from the gate. A first layer (16) of glass (2 % BSG) is used to provide the source of doping for the tip region and a second layer (35) of glass (6 % BSG) is used to provide the dopant for the more heavily doped major portion of source and drain regions. Spacers (30, 31) are formed between the glass layers to define the tip region from the main portion of the source and drain regions.		